

ABSTRACT OF THE DISCLOSURE

The first present invention provides a nitride based
5 semiconductor photo-luminescent device having an active layer having a quantum well structure, the active layer having both at least a high dislocation density region and at least a low dislocation density region lower in dislocation density than the high dislocation density region,
10 wherein the low dislocation density region includes a current injection region into which a current is injected, and the active layer is less than $1 \times 10^{18} \text{ m}^{-3}$ in impurity concentration.